L Number	Hits	S arch Text	DB	Time stamp
1	5583	(gat adj l ctr de) and ((titanium adj	USPAT;	2004/06/02
	•	nitride) or TiN) and sili id	US-PGPUB;	15:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	332	(gate adj electrode) and ((titanium adj	USPAT;	2004/06/02
		nitride) or TiN) and silicide and ((fig or fig.	US-PGPUB;	15:13
		or figure) near10 electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	246	(gate adj electrode) and ((titanium adj	USPAT;	2004/06/02
		nitride) or TiN) and silicide and ((fig or fig.	US-PGPUB;	15:13
		or figure) near10 electrode) and (method or	EPO; JPO;	
		process).ti,ab,clm.	DERWENT;	
			IBM_TDB	
4	52	(gate adj electrode) and ((titanium adj	USPAT;	2004/06/02
		nitride) or TiN) and silicide and ((fig or fig.	US-PGPUB;	15:14
		or figure) near10 electrode) and (method or	EPO; JPO;	
		process).ti,ab,clm. and (barrier adj layer)	DERWENT;	
			IBM_TDB	
5	12	(gate adj electrode) and ((titanium adj	USPAT;	2004/06/02
İ		nitride) or TiN) and silicide and ((fig or fig.	US-PGPUB;	15:15
		or figure) near10 electrode) and (method or	EPO; JPO;	
		process).ti,ab,clm. and (barrier adj layer)	DERWENT;	
		and (tin or (titanium near nitride)).ti,ab,clm.	IBM_TDB	
6	499	(gate adj electrode) and ((titanium adj	USPAT;	2004/06/02
		nitride) or TiN) and silicide and (method or	US-PGPUB;	15:15
		process).ti,ab,clm. and (barrier adj layer)	EPO; JPO;	
		and (tin or (titanium near nitride)).ti,ab,clm.	DERWENT;	
			IBM_TDB	
7	183	(gate adj electrode).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitride) or TiN) and silicide	US-PGPUB;	15:16
		and (method or process).ti,ab,clm. and	EPO; JPO;	
		(barrier adj layer) and (tin or (titanium near	DERWENT;	
_		nitride)).ti,ab,clm.	IBM_TDB	
8	111	(gate adj electrode).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitride) or TiN) and silicide	US-PGPUB;	15:16
		and (method or process).ti,ab,clm. and	EPO; JPO;	
		(barrier adj layer).ti,ab,clm. and (tin or	DERWENT;	
	440	(titanium near nitride)).ti,ab,clm.	IBM_TDB	0004/00/00
9	110	(gate adj electrode).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitride) or TiN).ti,ab,clm. and	US-PGPUB;	15:16
		silicide and (method or process).ti,ab,clm.	EPO; JPO;	
		and (barrier adj layer).ti,ab,clm. and (tin or	DERWENT;	
10	70	(titanium near nitride)).ti,ab,clm.	IBM_TDB	2004/20/22
	76	(gate adj lectrod).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitride) or TiN).ti,ab,clm. and	US-PGPUB;	15:17
		silicide.ti,ab,clm. and (m thod or	EPO; JPO;	
		process).ti,ab,clm. and (barri r adj	DERWENT;	
		layer).ti,ab, lm. and (tin r (titanium near nitrid)).ti,ab,clm.	IBM_TDB	

11	86	(gat adj lectr de).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitrid) or TiN).ti,ab,clm. and	US-P PUB;	15:17
		silicide.ti,ab,clm. and (meth d or	EPO; JPO;	
1		pr c ss).ti,ab,clm. and (barri r near2	DERWENT;	
		layer).ti,ab, lm. and (tin r (titanium n ar	IBM_TDB	
		nitride)).ti,ab,clm.		
12	19	(gate adj electrode).ti,ab,clm. and	USPAT;	2004/06/02
		((titanium adj nitride) or TiN).ti,ab,clm. and	US-PGPUB;	15:20
		silicide.ti,ab,clm. and (method or	EPO; JPO;	
		process).ti,ab,clm. and (barrier near2	DERWENT;	
		layer).ti,ab,clm. and (tin or (titanium near	IBM_TDB	
		nitride)).ti,ab,clm. and (electrode same	_	
		(film or layer) same barrier same ((titanium		
		near nitride) or tin)).ti,ab,clm.		
13	0	09/9922804	USPAT;	2004/06/02
			US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	1	09/922804	USPAT:	2004/06/02
			US-PGPUB;	15:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	4374	(titanium near silicide) near5 (form or	USPAT;	2004/06/02
		forming or formed)	US-PGPUB;	15:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	1255	electrode.clm. and (titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)	US-PGPUB;	15:23
			EPO; JPO;	
	-		DERWENT;	
			IBM_TDB	
17	207	electrode.clm. and ((titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)) and	US-PGPUB;	15:23
	1	(titanium adj nitride).clm.	EPO; JPO;	
			DERWENT;	
	.]		IBM_TDB	
18	61	electrode.clm. and ((titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)) and	US-PGPUB;	15:23
		(titanium adj nitride).clm. and barrier.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	40	electrode.clm. and ((titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)) and	US-PGPUB;	15:24
		((titanium adj nitride) near10 barrier).clm.	EPO; JPO;	
i			DERWENT;	
			IBM_TDB	

20	1	ele trod .clm. and ((titanium n ar silicid)	USPAT;	2004/06/02
		near5 no near5 (frm rfrming rfrm d))	US-PGPUB;	15:24
		and ((titanium adj nitrid) near10	EPO; JP ;	
		barrier).clm.	DERWENT;	
		,	IBM_TDB	
21	40	electr de.clm. and ((titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)) and	US-PGPUB;	15:25
		((titanium adj nitride) near10 barrier).clm.	EPO; JPO;	
		((DERWENT;	
			IBM_TDB	
22	0	(electrode.clm. and ((titanium near silicide)	USPAT;	2004/06/02
		near5 (form or forming or formed)) and	US-PGPUB;	15:25
		((titanium adj nitride) near10 barrier).clm.)	EPO; JPO;	13.23
		not silicide	, , ,	
		ilot silicide	DERWENT;	
23	742	(/titanium adi mitrida) manuf hamiau) alu	IBM_TDB	2004/06/02
23	742	((titanium adj nitride) near5 barrier).clm.	USPAT;	
			US-PGPUB;	15:25
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
24	85	((titanium adj nitride) near5 barrier).clm.	USPAT;	2004/06/02
		and (gate adj electrode).clm.	US-PGPUB;	15:25
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
25	32	(((titanium adj nitride) near5 barrier).clm.	USPAT;	2004/06/02
		and (gate adj electrode).clm.) not silicide	US-PGPUB;	15:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	1	((((titanium adj nitride) near5 barrier).clm.	USPAT;	2004/06/02
		and (gate adj electrode).clm.) not silicide)	US-PGPUB;	15:28
		and (electrode same (silicon or polysilicon)	EPO; JPO;	
		same (titanium adj nitride)).clm.	DERWENT;	
			IBM_TDB	
27	160	(electrode same (silicon or polysilicon)	USPAT;	2004/06/02
		same (titanium adj nitride)).clm.	US-PGPUB;	15:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	576	(electrode same (silicon or polysilicon)	USPAT;	2004/06/02
		same (titanium adj nitride)).ti,ab,clm.	US-PGPUB;	15:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
29	323	((electrode same (silicon or polysilicon)	USPAT;	2004/06/02
		same (titanium adj nitride)).ti,ab,clm.) not	US-PGPUB;	15:28
		silicid	EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	

30	91	(((electrod same (silicon r p lysilicon)	USPAT;	2004/06/02
		same (titanium adj nitride)).ti,ab, lm.) n t	US-PGPUB;	15:29
		silicid) and (ann al rann aled r	EPO; JPO;	
		ann aling or tr at or treating r treated or	DERWENT;	
	1	tr atment or cure or cur d or uring)	IBM_TDB	
31	66	(((el ctrode sam (ilic n r polysilic n)	USPAT;	2004/06/02
••		same (titanium adj nitride)).ti,ab,clm.) not	US-PGPUB;	15:29
		silicide) and (anneal or annealed or	EPO; JPO;	13.23
		annealing or treat or treating or treated or	DERWENT;	
		treatment or cure or cured or	1	
	İ		IBM_TDB	
22	20	curing).ti,ab,clm.		0004/00/00
33	20	(((electrode same (silicon or polysilicon)	USPAT;	2004/06/02
		same (titanium adj nitride)).ti,ab,clm.) not	US-PGPUB;	15:33
		silicide) and (anneal or annealed or	EPO; JPO;	
		annealing or treat or treating or treated or	DERWENT;	
		treatment or cure or cured or	IBM_TDB	
		curing).ti,ab,clm. and		
		temperature.ti,ab,clm.		
34	10	(methodor or process) same electrode	USPAT;	2004/06/02
		same (silicon or polysilicon or poly-silicon)	US-PGPUB;	15:54
		same (barrier near5 (titanium adj	EPO; JPO;	i
		nitride)).ti,ab,clm.	DERWENT;	
			IBM_TDB	
35	643	(electrode near20 polysilicon near20	USPAT;	2004/06/02
		(barrier near2 layer))	US-PGPUB;	15:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
36	65	(electrode near20 polysilicon near20	USPAT;	2004/06/02
		(barrier near2 layer)).clm.	US-PGPUB;	15:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
37	11	(electrode near20 polysilicon near20	USPAT;	2004/06/02
		(barrier near2 layer)).clm. and ((barrier	US-PGPUB;	15:58
		near2 layer) near20 (titanium near	EPO; JPO;	
		nitride)).clm.	DERWENT;	
		"	IBM TDB	
38	3	((electrode near20 polysilicon near20	USPAT;	2004/06/02
		(barrier near2 layer)).clm. and ((barrier	US-PGPUB;	16:01
		near2 layer) near20 (titanium near	EPO; JPO;	
		nitride)).clm.) not silicide	DERWENT;	
		,	IBM_TDB	
39	2	(((electrode near20 polysilicon near20	USPAT;	2004/06/02
	-	(barrier near2 layer)).clm. and ((barrier	US-PGPUB;	16:02
		near2 layer) near20 (titanium near	EPO; JPO;	
		nitride)).clm.) not silicide) and (anneal or	DERWENT;	
		annealing or annealed)	IBM_TDB	
	'		D.m_100	

40	2	(((lectrode near20 polysilic n near20	USPAT;	2004/06/02
		(barrier n ar2 lay r)).clm. and ((barrier	US-P PUB;	16:02
		n ar2 lay r) n ar20 (titanium near	EPO; JPO;	
		nitride)).clm.) n t silicide) and (anneal or	DERWENT;	
		ann aling or anneal der treat or treating or	IBM_TDB	
		tr ated or treatment)		
41	2	(((electrode near20 polysilicon near20	USPAT;	2004/06/02
		(barrier near2 layer)).clm. and ((barrier	US-PGPUB;	16:03
:		near2 layer) near20 (titanium near	EPO; JPO;	
		nitride)).clm.) not silicide) and (heat or	DERWENT;	
		heated or heating or anneal or annealing or	IBM_TDB	
		annealed or treat or treating or treated or		
		treatment)		